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Microsemi.

Power Matters[™]

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Overview

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.60	V
DC Current Gain	HFE	20.00		60.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			80.00	V
Collector Current (dc)	I _C			5.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			80.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			6.00	V
Power Dissipation, Total	P _T			52.00	W

This part can be found in the following product categories:

- Discretes ► Transistors ► BJT(BiPolar Junction Transistor) ► PNP Transistor
- Non-Radiation Hardened Devices Transistors BJT(BiPolar Junction Transistor) PNP Transistor

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